

Amendments to the Claims

1. (Cancelled).
2. (Previously presented) The method of claim 10 wherein there is no O₂ flowed into the chamber during the forming the vapor mixture and deposition.
3. (Previously presented) The method of claim 10 wherein the evaporating the aluminum oxide comprises thermal evaporation of the aluminum oxide from the single crystal sapphire.
4. (Cancelled).
5. (Previously presented) The method of claim 10 wherein the evaporating the aluminum oxide comprises ion beam evaporation of the aluminum oxide from the single crystal sapphire.
6. (Previously presented) The method of claim 10 wherein the evaporating the aluminum oxide comprises electron gun evaporation of the aluminum oxide from the single crystal sapphire.
7. (Cancelled).

8. (Previously presented) The method of claim 10 wherein the substrate comprises silicon.

9. (Previously presented) The method of claim 10 wherein the substrate comprises monocrystalline silicon.

10. (Currently amended) A method of forming an assembly comprising silicon-doped porous aluminum oxide, comprising:

evaporating aluminum oxide from a single crystal sapphire;

evaporating silicon monoxide from a source comprising of silicon monoxide;

forming a vapor mixture comprising the evaporated aluminum oxide and evaporated silicon monoxide in a reaction chamber;

depositing at least some of the mixture of evaporated aluminum oxide and silicon monoxide on a semiconductive material substrate to form the silicon-doped porous aluminum oxide on the substrate, an amount of silicon present in the silicon-doped aluminum oxide being controlled by controlling the evaporation rate during the evaporating silicon monoxide; and

forming a conductive material on the deposited silicon-doped porous aluminum oxide, the conductive material being separated from the semiconductive material of the substrate by the silicon-doped porous aluminum oxide.

Claims 11-30 (Cancelled).

31. (Previously presented) The method of claim 10 wherein the silicon-doped porous aluminum oxide contains from 0.1 percent to about 30 weight percent of silicon dopant, by weight.

32. (Previously presented) The method of claim 10 wherein the semiconductive material substrate is room temperature during the depositing.